

### **Amendments to the Claims**

This listing of the Claims will replace all prior versions and listings of the claims in this patent application.

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#### **Listing of Claims**

Claims 1-241 (canceled)

- 10 242. (currently amended) A method for fabricating a chip package<sub>2</sub> comprising:  
    joining a die and a substrate, wherein said die has a top surface at a horizontal level, wherein said die and said substrate are under said horizontal level;  
    after said joining said die and said substrate, forming a patterned circuit layer over said horizontal level, wherein said patterned circuit layer extends across an edge  
15 of said die;  
    after said joining said die and said substrate, forming a passive device over said substrate and over said horizontal level, wherein said passive device comprises a part not directly over any die in said chip package; and  
    after said forming said patterned circuit layer and said forming said passive  
20 device, separating said substrate into multiple portions.

243. (currently amended) A method for fabricating a chip package<sub>2</sub> comprising:  
    providing a first die having a ~~first~~ top surface at a horizontal level;  
    providing a second die having a ~~second~~ top surface at said horizontal level;  
25 forming a polymer between said first and second dies;  
    after said forming said polymer, forming a passive device over said horizontal level, wherein said passive device has a first ~~connection point~~ terminal connected to said first die; and  
    after said forming said passive device, forming a metal bump over said  
30 horizontal level, wherein said metal bump is connected to a second terminal

~~connection point~~ of said passive device.

244. (currently amended) A method for fabricating a chip package, comprising:

- providing a first die having a ~~first~~ top surface at a horizontal level;
- 5 providing a second die having a ~~second~~ top surface at said horizontal level;
- forming a polymer between said first and second dies;
- after said forming said polymer, forming a passive device over said horizontal level, wherein said passive device has a part not directly over any die in said chip package;
- 10 after said forming said passive device over said horizontal level, forming an insulating layer on said passive device and over said horizontal level; and
- after said forming said polymer, forming a patterned circuit layer over said horizontal level, wherein said patterned circuit layer extends across an edge of said first ~~or second~~ die.

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245. (previously presented) The method of claim 242, wherein said substrate comprises a metal substrate.

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246. (currently amended) The method of claim 242 further comprising joining a film and said substrate, wherein an opening in said film exposes said substrate, followed by said joining said die and said substrate, wherein said die is in ~~exposed by~~ said opening.

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247. (previously presented) The method of claim 246, wherein forming said opening in said film comprises a punching process.

248. (previously presented) The method of claim 246, wherein said film comprises a metal layer.

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Claim 249 (canceled)

250. (previously presented) The method of claim 242, wherein said forming said patterned circuit layer comprises an electroplating process.

5 251. (previously presented) The method of claim 242, wherein said forming said patterned circuit layer comprises a sputtering process.

252. (previously presented) The method of claim 242, wherein said forming said passive device comprises an electroplating process.

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253. (withdrawn) The method of claim 242, wherein said forming said passive device comprises a sputtering process.

15 254. (previously presented) The method of claim 242, after said joining said die and said substrate, further comprising forming a solder bump over said horizontal level, followed by said separating said substrate.

20 255. (withdrawn) The method of claim 242, after said joining said die and said substrate, further comprising forming a gold bump over said horizontal level, followed by said separating said substrate.

256. (previously presented) The method of claim 242, wherein said passive device comprises an inductor.

25 257. (currently amended) The method of claim 243 further comprising joining said first die and a substrate and joining said second die and said substrate, followed by said forming said polymer further on said substrate.

30 258. (previously presented) The method of claim 257, wherein said substrate comprises a metal substrate.

259. (previously presented) The method of claim 257, after said forming said metal bump, further comprising separating said substrate into multiple portions.

5 260. (previously presented) The method of claim 243, wherein said polymer comprises an epoxy.

261. (currently amended) The method of claim 243, after said forming said polymer, further comprising forming a patterned circuit layer over said horizontal level and  
10 over said polymer, wherein said patterned circuit layer extends across an edge of said first die, followed by said forming said metal bump.

262. (previously presented) The method of claim 261, wherein said forming said patterned circuit layer comprises an electroplating process.

15 263. (previously presented) The method of claim 261, wherein said forming said patterned circuit layer comprises a sputtering process.

264. (previously presented) The method of claim 243, wherein said forming said  
20 passive device comprises an electroplating process.

265. (withdrawn) The method of claim 243, wherein said forming said passive device comprises a sputtering process.

25 266. (currently amended) The method of claim 243, wherein said forming said metal bump comprises forming a solder bump over said horizontal level, wherein said solder bump is connected to said second terminal. ~~connection point~~.

267. (withdrawn – currently amended) The method of claim 243, wherein said forming said metal bump comprises forming a gold bump over said horizontal level, wherein said gold bump is connected to said second terminal. ~~connection point~~.

5 268. (previously presented) The method of claim 243, wherein said passive device comprises an inductor.

269. (previously presented) The method of claim 244, wherein said forming said patterned circuit layer comprises an electroplating process.

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270. (previously presented) The method of claim 244, wherein said forming said patterned circuit layer comprises a sputtering process.

15 271. (previously presented) The method of claim 244, wherein said forming said passive device comprises an electroplating process.

272. (withdrawn) The method of claim 244, wherein said forming said passive device comprises a sputtering process.

20 273. (previously presented) The method of claim 244, after said forming said insulating layer and said forming said patterned circuit layer, further comprising forming a solder bump over said horizontal level.

25 274. (withdrawn) The method of claim 244, after said forming said insulating layer and said forming said patterned circuit layer, further comprising forming a gold bump over said horizontal level.

275. (previously presented) The method of claim 244, wherein said passive device comprises an inductor.

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276. (previously presented) The method of claim 244, wherein said passive device comprises a capacitor.

5 277. (previously presented) The method of claim 244, wherein said passive device comprises a resistor.

278. (previously presented) The method of claim 244, wherein said passive device comprises a filter.

10 279. (previously presented) The method of claim 244, wherein said polymer comprises an epoxy.

280. (currently amended) The method of claim 244 further comprising joining said first die and a substrate and joining said second die and said substrate, followed by  
15 said forming said polymer further on said substrate.

281. (previously presented) The method of claim 280, wherein said substrate comprises a metal substrate.

20 282. (previously presented) The method of claim 280, after said forming said insulating layer and said forming said patterned circuit layer, further comprising separating said substrate into multiple portions.

283. (previously presented) The method of claim 242, wherein said passive device  
25 comprises a capacitor.

284. (previously presented) The method of claim 242, wherein said passive device comprises a resistor.

285. (previously presented) The method of claim 242, wherein said passive device comprises a filter.

5 286. (previously presented) The method of claim 243, wherein said passive device comprises a capacitor.

287. (previously presented) The method of claim 243, wherein said passive device comprises a resistor.

10 288. (previously presented) The method of claim 243, wherein said passive device comprises a filter.